



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I_D max $T_A = +25$ °C
	110mΩ @ $V_{GS} = 4.5V$	2A
20V	145mΩ @ V _{GS} = 2.5V	1.7A
	230mΩ @ V _{GS} = 1.8V	1.3A

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Boost Application
- Analog Switch

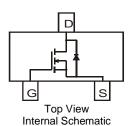
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.008 grams (Approximate)



SOT23

Top View



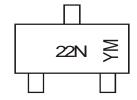
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2230UQ-7	SOT23	3,000/Tape & Reel
DMN2230UQ-13	SOT23	10,000/Tape & Reel

Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



22N = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

2010 0000 1	- ,											
Year	2007	2008	2009	2010	201	1 20	12	2013	2014	2015	2016	2017
Code	U	V	W	X	Y		Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±12	V
Drain Current (Note 6)	I _D	2.0	Α
Pulsed Drain Current (Note 7)	I _{DM}	7	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P_{D}	600	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	208	°C/W
Operating and Storage Temperature Range	T_{J} , T_{STG}	-55 to +150	°C

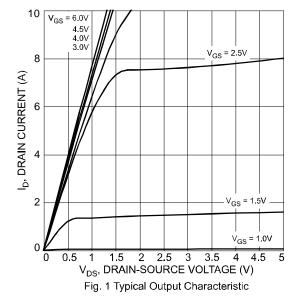
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

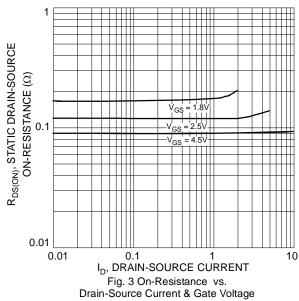
		1	1			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	_	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}			±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	_	1.0	V	$V_{DS} = V_{CS}, I_D = 250 \mu A$
			81	110		$V_{GS} = 4.5V, I_D = 2.5A$
Static Drain-Source On-Resistance	R _{DS} (ON)		113 170	145	mΩ	$V_{GS} = 2.5V, I_D = 1.5A$
				230		$V_{GS} = 1.8V, I_D = 1.0A$
Forward Transfer Admittance	Y _{fs}	_	5	—	S	$V_{DS} = 5V, I_{D} = 2.4A$
Diode Forward Voltage (Note 8)	V_{SD}		0.8	1.1	V	$V_{GS} = 0V, I_S = 1.05A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_	188		pF	101111
Output Capacitance	Coss	_	44	_	pF	$V_{DS} = 10V$, $V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss		30		рF	1 = 1.000112
Total Gate Charge	Q_{g}		2.3		nC	
Gate-Source Charge	Qgs		0.3		nC	$V_{DS} = 10V, I_{D} = 11.6A$
Gate-Drain Charge	Q_{gd}		0.5		nC	
Turn-On Delay Time	t _{d(on)}	_	8	_		
Rise Time	t _r	_	3.8	_	ns	$V_{DD} = 10V$, $R_L = 10\Omega$
Turn-Off Delay Time	t _{d(off)}	_	19.6	_	115	$I_D = 1A$, $V_{GEN} = 4.5V$, $R_G = 6\Omega$
Fall Time	t _f		8.3	_		

Notes:

- Device mounted on FR-4 PCB, or minimum recommended pad layout.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.







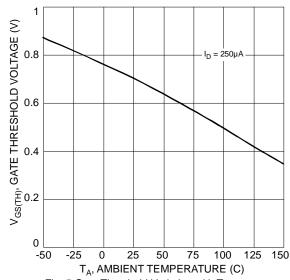
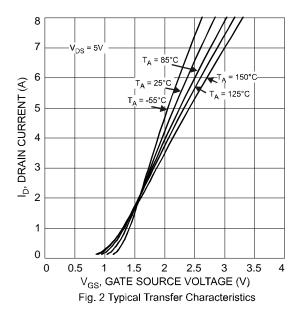


Fig. 5 Gate Threshold Variation with Temperature



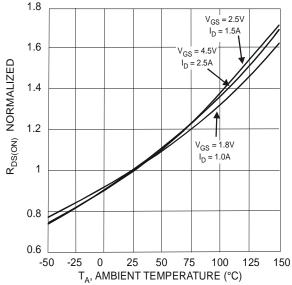
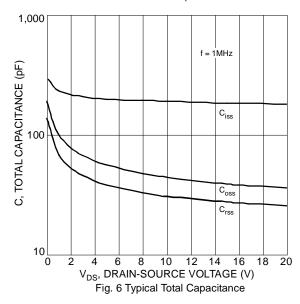
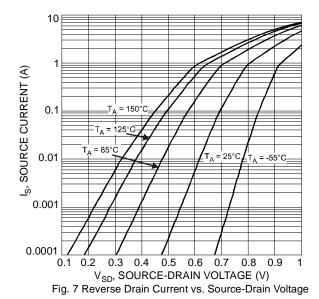
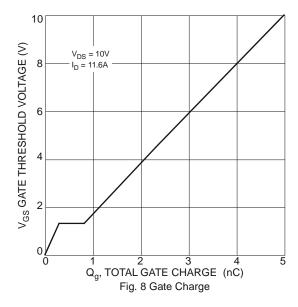


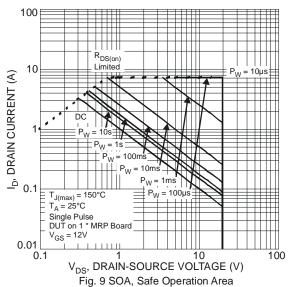
Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





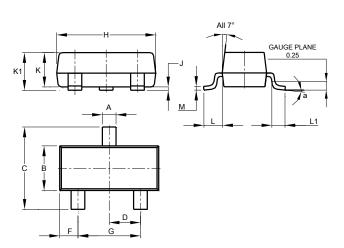






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

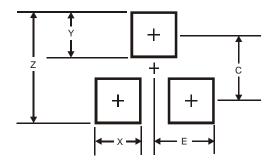


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	a 8°					
All Dimensions in mm						



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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